

METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING
SEMICONDUCTOR DEVICE, PROGRAM, AND SUBSTRATE PROCESSING
APPARATUS

ABSTRACT

A technique includes (a) preparing a substrate including a first film formed inside a recess, a surface of the first film inside the recess being terminated with a first termination that reduces wettability with respect to a processing liquid; and (b) removing at least a portion of the first film formed in a first region on an opening side of the recess while leaving the first film formed in a second region on a bottom side of the recess by supplying the processing liquid to the substrate and selectively exposing, to the processing liquid, the surface of the first film formed in the first region with respect to the surface of the first film formed in the second region.

Figs. 7B and 7C